# MM74HCT245 Octal 3-STATE Transceive

# FAIRCHILD

SEMICONDUCTOR

## MM74HCT245 Octal 3-STATE Transceiver

### **General Description**

The MM74HCT245 3-STATE bi-directional buffer utilizes advanced silicon-gate CMOS technology and is intended for two-way asynchronous communication between data buses. It has high drive current outputs which enable high speed operation even when driving large bus capacitances. This circuit possesses the low power consumption of CMOS circuitry, yet has speeds comparable to low power Schottky TTL circuits.

This device is TTL input compatible and can drive up to 15 LS-TTL loads, and all inputs are protected from damage due to static discharge by diodes to  $V_{CC}$  and ground.

The MM74HCT245 has one active low enable input  $(\overline{G})$ , and a direction control (DIR). When the DIR input is HIGH, data flows from the A inputs to the B outputs. When DIR is LOW, data flows from B to A.

MM74HCT devices are intended to interface between TTL and NMOS components and standard CMOS devices. These parts are also plug-in replacements for LS-TTL devices and can be used to reduce power consumption in existing designs.

### **Ordering Code:**

Order Number Package Number Package Description					
MM74HCT245WM	0	20-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-013, 0.300" Wide			
MM74HCT245SJ		20-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide			
MM74HCT245MTC MTC20 20-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm W					
MM74HCT245N	N20A	20-Lead Plastic Dual-In-Line Package (PDIP), JEDEC MS-001, 0.300" Wide			
Devices also available in Tape and Reel. Specify by appending the suffix letter "X" to the ordering code.					

### **Connection Diagram**

### **Truth Table**

**Features** 

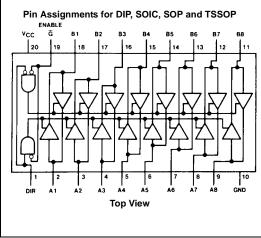
■ TTL input compatible

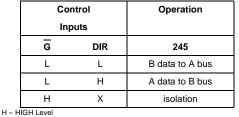
■ 3-STATE outputs for connection to system busses

■ High output drive current: 6 mA (min)

■ Low power: 80 µA (74HCT Series)

■ High speed: 16 ns typical propagation delay

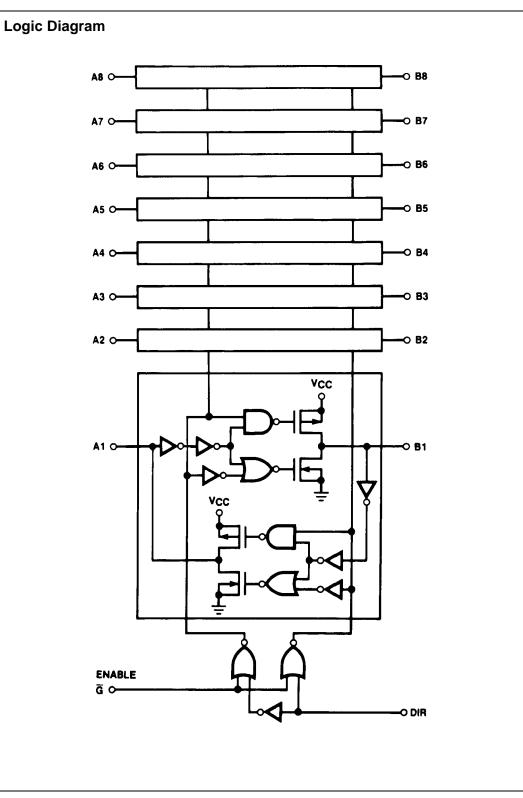




L = LOW Level X = Irrelevant

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### Absolute Maximum Ratings(Note 1)

	J = ( )
(Note 2)	
Supply Voltage (V <sub>CC</sub> )	-0.5 to +7.0V
DC Input Voltage (V <sub>IN</sub> )	–1.5 to V <sub>CC</sub> +1.5V
DC Output Voltage (V <sub>OUT</sub> )	–0.5 to V <sub>CC</sub> +0.5V
Clamp Diode Current (I <sub>IK</sub> , I <sub>OK</sub> )	±20 mA
DC Output Current,	±35 mA
DC $V_{CC}$ or GND Current, per pin (I <sub>CC</sub> )	±70 mA
Storage Temperature Range (T <sub>STG</sub> )	–65°C to +150°C
Power Dissipation (P <sub>D</sub> )	
(Note 3)	600 mW
S.O. Package only	500 mW
Lead Temperature (TL)	
(Soldering 10 seconds)	260°C

# Recommended Operating Conditions

	Min	Max	Units		
Supply Voltage (V <sub>CC</sub> )	4.5	5.5	V		
DC Input or Output Voltage					
(V <sub>IN</sub> , V <sub>OUT</sub> )	0	V <sub>CC</sub>	V		
Operating Temperature Range (T <sub>A</sub> )	-40	+85	°C		
Input Rise or Fall Times					
(t <sub>r</sub> , t <sub>f</sub> )		500	ns		
Note 1: Absolute Maximum Ratings are those values beyond which damage to the device may occur.					

**MM74HCT245** 

Note 2: Unless otherwise specified all voltages are referenced to ground. Note 3: Power Dissipation temperature derating — plastic "N" package: – 12 mW/°C from 65°C to 85°C.

### **DC Electrical Characteristics**

Symbol	Parameter	Conditions	T <sub>A</sub> = 25°C		$T_A = -40$ to $85^{\circ}C$	$T_A = -55$ to $125^{\circ}C$	Units	
			Тур	Guaranteed Limits			Units	
VIH	Minimum HIGH Level Input Voltage			2.0	2.0	2.0	V	
V <sub>IL</sub>	Maximum LOW Level Input Voltage			0.8	0.8	0.8	V	
V <sub>OH</sub>	Minimum HIGH Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$						
	Output Voltage	I <sub>OUT</sub>   = 20 μA	V <sub>CC</sub>	V <sub>CC</sub> - 0.1	V <sub>CC</sub> - 0.1	V <sub>CC</sub> - 0.1	V	
		$ I_{OUT}  = 6.0 \text{ mA}, V_{CC} = 4.5 \text{V}$	4.2	3.98	3.84	3.7	V	
		$ I_{OUT}  = 7.2 \text{ mA}, V_{CC} = 5.5 \text{V}$	5.2	4.98	4.84	4.7	V	
V <sub>OL</sub>	Maximum LOW Level	$V_{IN} = V_{IH} \text{ or } V_{IL}$						
	Voltage	I <sub>OUT</sub>   = 20 μA	0	0.1	0.1	0.1	V	
		$ I_{OUT}  = 6.0 \text{ mA}, V_{CC} = 4.5 \text{V}$	0.2	0.26	0.33	0.4	V	
		$ I_{OUT}  = 7.2 \text{ mA}, V_{CC} = 5.5 \text{V}$	0.2	0.26	0.33	0.4	V	
I <sub>IN</sub>	Maximum Input	$V_{IN} = V_{CC}$ or GND,		±0.1	±1.0	±1.0	μA	
	Current	$V_{IH}$ or $V_{IL}$ , Pin 1 or 19						
l <sub>oz</sub>	Maximum 3-STATE	V <sub>OUT</sub> = V <sub>CC</sub> or GND		±0.5	±5.0	±10	μA	
	Output Leakage	$\overline{G} = V_{IH}$						
	Current							
I <sub>CC</sub>	Maximum Quiescent	$V_{IN} = V_{CC}$ or GND		8	80	160	μA	
	Supply Current	$I_{OUT} = 0 \ \mu A$						
		V <sub>IN</sub> = 2.4V or 0.5V (Note 4)	0.6	1.0	1.3	1.5	mA	

Note 4: Measured per input. All other inputs at  $\mathsf{V}_{\mathsf{CC}}$  or ground.

### **AC Electrical Characteristics**

 $V_{CC}$  = 5.0V,  $t_{f}$  =  $t_{f}$  = 6 ns,  $T_{A}$  = 25°C (unless otherwise specified)

Symbol	Parameter	Conditions	Тур	Guaranteed Limit	Units
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Output	C <sub>L</sub> = 45 pF	16	20	ns
	Propagation Delay				
t <sub>PZL</sub> , t <sub>PZH</sub>	Maximum Output	C <sub>L</sub> = 45 pF	29	40	ns
	Enable Time	$R_L = 1 k\Omega$			
t <sub>PLZ</sub> , t <sub>PHZ</sub>	Maximum Output	$C_L = 5 \text{ pF}$	20	25	ns
I	Disable Time	$R_L = 1 k\Omega$			

### **AC Electrical Characteristics**

 $V_{CC}$  = 5.0V  $\pm$  10%,  $t_r$  =  $t_f$  = 6 ns (unless otherwise specified)

Symbol	Parameter	Conditions	T <sub>A</sub> =	25°C	$T_A = -40$ to $85^{\circ}C$	$T_{A}{=}{-}55$ to $125^{\circ}C$	Units
			Тур	Typ Guaranteed Limits			Units
t <sub>PHL</sub> , t <sub>PLH</sub>	Maximum Output	C <sub>L</sub> = 50 pF	17	23	29	34	ns
	Propagation Delay	$C_L = 150 \text{ pF}$	24	30	38	45	ns
t <sub>PZL</sub>	Maximum Output	$R_L = 1 k\Omega$	31	42	53	63	ns
	Enable Time	$C_L = 50 \text{ pF}$					
t <sub>PZH</sub>	Maximum Output	$R_L = 1 k\Omega$	23	33	41	49	ns
	Enable Time	$C_L = 50 \text{ pF}$					
t <sub>PHZ</sub> , t <sub>PLZ</sub>	Maximum Output	$R_L = 1 k\Omega$	21	30	38	45	ns
	Disable Time	$C_L = 50 \text{ pF}$					
t <sub>THL</sub> , t <sub>TLH</sub>	Maximum Output	C <sub>L</sub> = 50 pF	8	12	15	18	ns
	Rise and Fall Time						
CIN	Maximum Input		10	15	15	15	pF
	Capacitance						
C <sub>OUT</sub>	Maximum Output/Input		20	25	25	25	pF
	Capacitance						
C <sub>PD</sub>	Power Dissipation	$\overline{G} = V_{CC}$ (Note 5)	7				pF
	Capacitance	G = GND	100				pF

Note 5:  $C_{PD}$  determines the no load power consumption,  $P_D = C_{PD} V_{CC} 2 f + I_{CC} V_{CC}$ , and the no load dynamic current consumption,  $I_S = C_{PD} V_{CC} f + I_{CC}$ .

